

Charge collection properties of irradiated CMOS detectors

Wednesday 7 June 2017 10:00 (20 minutes)

Results of E-TCT and Sr90 measurements with CMOS detectors produced by different foundries on p-type substrates with different initial resistivities will be presented. With Edge-TCT method the thickness of depleted layer of passive CMOS detectors was estimated and studied as a function of fluence. Collected charge deposited by MIPs from Sr90 source was measured with external amplifier. Collected charge measured with Sr90 will be compared with E-TCT measurements.

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